

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re New Patent Application of)
Kazuichiroh ITONAGA)
Japanese Priority Application No. 2000-302064) Attn: Applications
Japanese Priority Date: October 2, 2000) Branch
For: SEMICONDUCTOR DEVICE AND)
METHOD FOR MANUFACTURING)
THE SAME) Date: October 1, 2001

PRELIMINARY AMENDMENT

Honorable Commissioner for Patents
Washington, D.C. 20231

Sir:

Please preliminarily amend the subject application as follows:

IN THE SPECIFICATION:

Please amend the specification as follows: Please note that the amendment to the specification is presented below in its amended form. It is further presented as an Attachment to the Amendment whereby the amendments to the specification is outlined using the conventional method of bracketing and underlining.

On page 17, last paragraph through page 18, first paragraph, please amend as follows:

FIG. 9A and FIG. 9B are cross-sectional views illustrating some steps in the method for manufacturing a semiconductor device according to the fourth embodiment, from the removal of an unreacted second cobalt film up to the formation of a fourth silicide film.

REMARKS

The specification has been amended to correct the description of Figure 9 in
the Brief Description of the Drawings.

Examination on the merits is requested.

Respectfully submitted,


Eric J. Robinson
Registration No. 38,285

NIXON PEABODY LLP
8180 Greensboro Drive, Suite 800
McLean, Virginia 22102
(703) 790-9110

SEARCHED INDEXED SERIALIZED FILED

VERSION WITH MARKINGS TO SHOW CHANGES MADE

FIG. 9A and FIG. 9B [FIG. 9A to FIG 9C] are cross-sectional views illustrating some steps in the method for manufacturing a semiconductor device according to the fourth embodiment, from the removal of an unreacted second cobalt film up to the formation of a fourth silicide film.

TOP SECRET//SI//FOUO//G